N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- DC/DC Conversion
- Power Routing
- Motor Drives

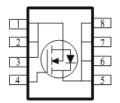
PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)	
30	$3 @ V_{GS} = 4.5V$	34	
30	$4.2 @ V_{GS} = 2.5V$	29	



ROHS
COMPLIANT
HALOGEN



DFN5X6-8L



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Symbol Limit			
Drain-Source Voltage			30	V		
Gate-Source Voltage		V_{GS}	±12	V		
Continuous Drain Current a	T _A =25°C	l L	34			
Continuous Drain Current	T _A =70°C	· I _D	27	A		
Pulsed Drain Current ^b		I _{DM}	100			
Continuous Source Current (Diode Conduction) a		I _S	7.3	Α		
Power Dissipation ^a	T _A =25°C	P_{D}	5	W		
rower Dissipation	T _A =70°C	'D	3.2	V V		
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	65	C/VV			

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	0.5			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	50			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$			3 mΩ		
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 16 \text{ A}$			4.2	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		31		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.65 \text{ A}, V_{GS} = 0 \text{ V}$		0.69		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		107			
Gate-Source Charge	Q_{gs}	$I_{D} = 20 \text{ A}$		26		nC	
Gate-Drain Charge	Q_gd	1D = 20 A		26			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, R_{L} = 0.8 \Omega,$		42			
Rise Time	t _r	$V_{DS} = 13 \text{ V}, \text{ K}_{L} = 0.6 \Omega,$ $I_{D} = 20 \text{ A},$		102		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		310		ns	
Fall Time	t _f	VGEN - 4.5 V, NGEN - 0 12		100			
Input Capacitance	C _{iss}			23185			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		764		pF	
Reverse Transfer Capacitance	C_{rss}			763			

Notes

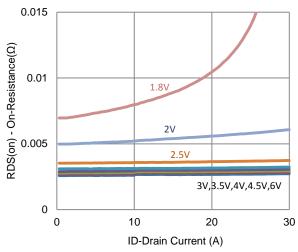
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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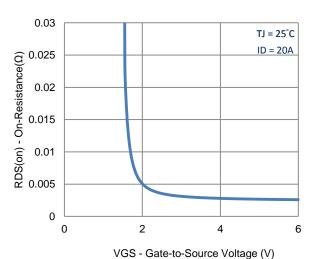
Typical Electrical Characteristics

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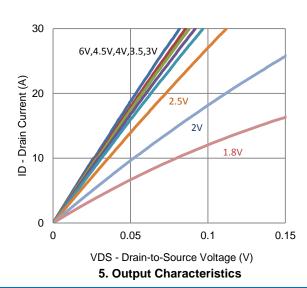
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1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



TJ = 25°C

40

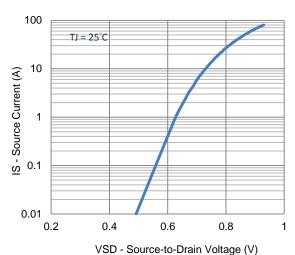
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VGS - Gate-to-Source Voltage (V)

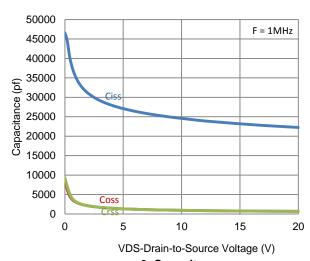
2. Transfer Characteristics

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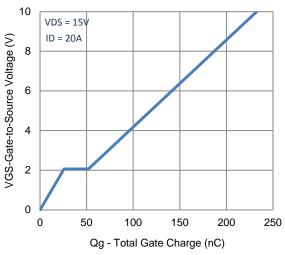


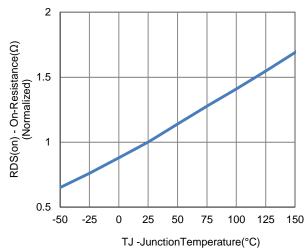
4. Drain-to-Source Forward Voltage



6. Capacitance

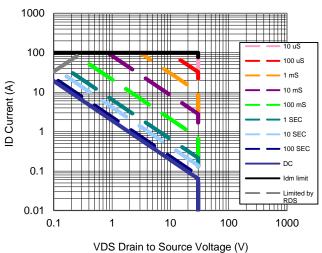
Typical Electrical Characteristics

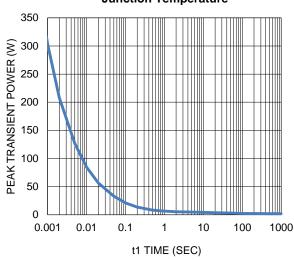




7. Gate Charge

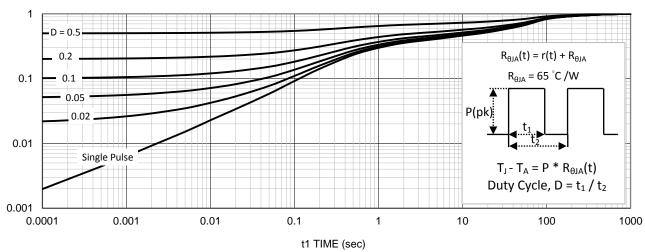






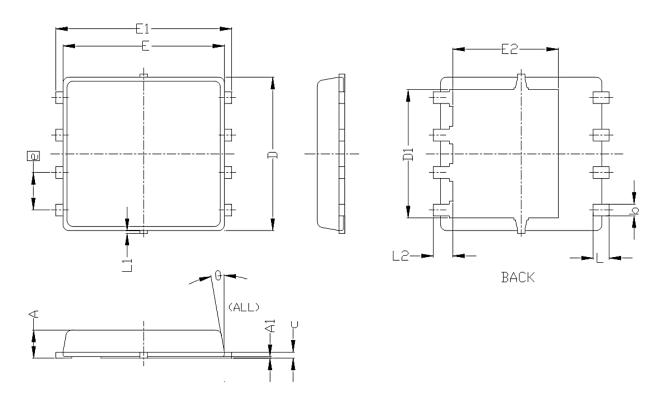
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.85	0.95	1.00	0.033	0.037	0.039
Al	0.00		0.05	0.000		0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
с	0. 15	0. 20	0. 25	0.006	0.008	0.010
D	5, 20 BSC			0. 205 BSC		
D1	4. 35 BSC			0. 171 BSC		
E	5, 55 BSC			0. 219 BSC		
E1	6. 05 BSC			0. 238 BSC		
E2	3. 62 BSC			0. 143 BSC		
e	1. 27 BSC			0. 050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0		0.15	0		0.006
L2	0.68 REF			0.027 REF		
θ	0°		10°	0°		10°